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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Applicant: Hongyong ZHANG et al.		Filing Date: August 18, 2003		Group: 2811	
U.S. PATENT DOCUMENTS									
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)			
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Examiner	Date Considered		11/16/04						
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not and not considered. Include copy of this form with next communication to applicant.									

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